



General Description

The HSU80N03 is the high cell density trench N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The HSU80N03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

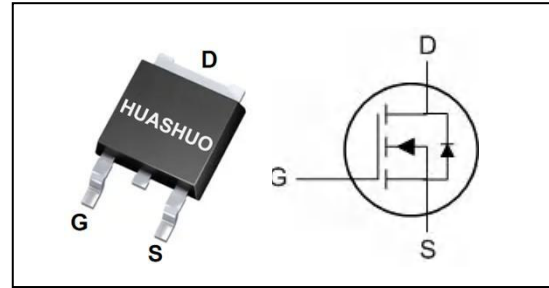
Product Summary

V_{DS}	30	V
$R_{DS(ON),TYP}$	4.5	m Ω
I_D	80	A

Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench Technology

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	57	A
I_{DM}	Pulsed Drain Current ²	320	A
EAS	Single Pulse Avalanche Energy ³	300	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	115	W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	2.4	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	50	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t $\leq$ 10s)	---	25	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.8	$^{\circ}C/W$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.028	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=30A$	---	4.5	6	$m\Omega$
		$V_{GS}=4.5V, I_D=15A$	---	6.5	10	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-6.16	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=30A$	20	---	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	---	1.7	3.4	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=30V, V_{GS}=10V, I_D=40A$	---	84	---	nC
Q_{gs}	Gate-Source Charge		---	14	---	
Q_{gd}	Gate-Drain Charge		---	30	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V, V_{GS}=10V, R_G=3\Omega$ $I_D=40A$	---	20	---	ns
T_r	Rise Time		---	15	---	
$T_{d(off)}$	Turn-Off Delay Time		---	50	---	
T_f	Fall Time		---	8	---	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	---	2290	---	pF
C_{oss}	Output Capacitance		---	360	---	
C_{rss}	Reverse Transfer Capacitance		---	280	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	80	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	160	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=40A, dI/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	32	---	nS
Q_{rr}	Reverse Recovery Charge		---	60	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=53.8A$
- 4.The power dissipation is limited by 175°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

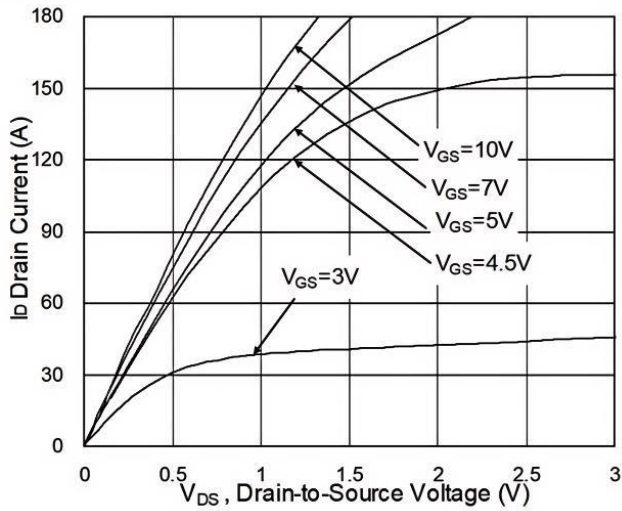


Fig.1 Typical Output Characteristics

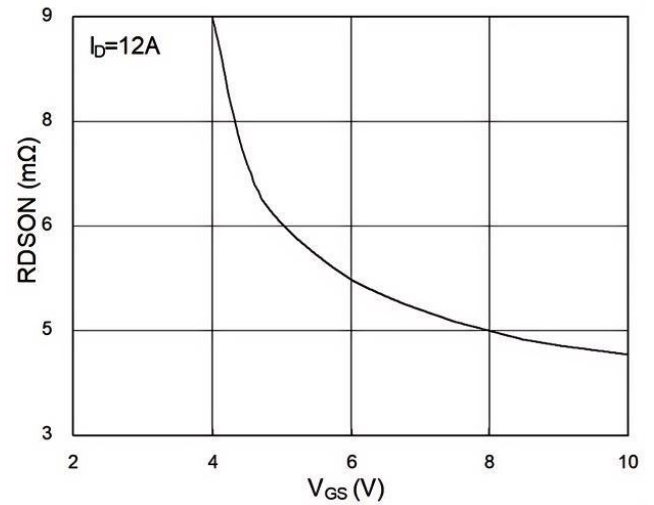


Fig.2 On-Resistance vs. G-S Voltage

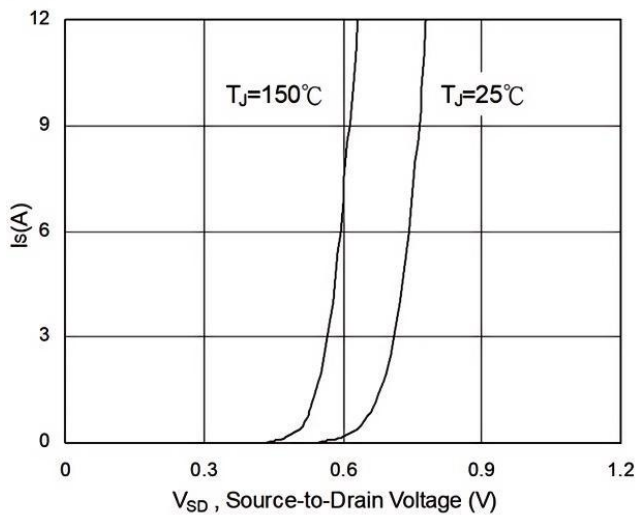


Fig.3 Forward Characteristics of Reverse

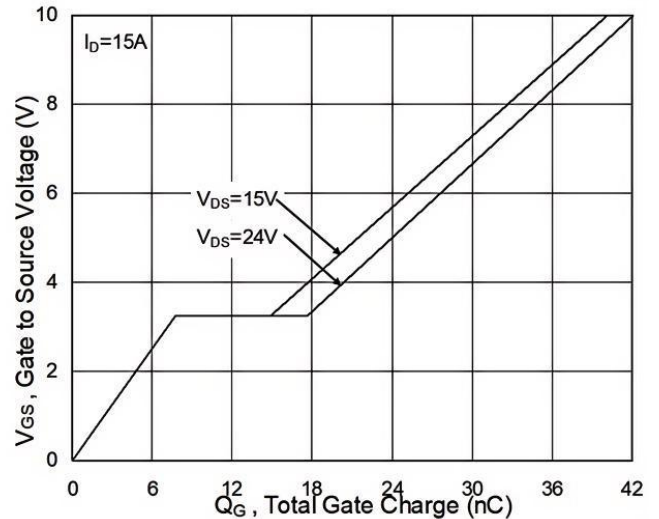


Fig.4 Gate-Charge Characteristics

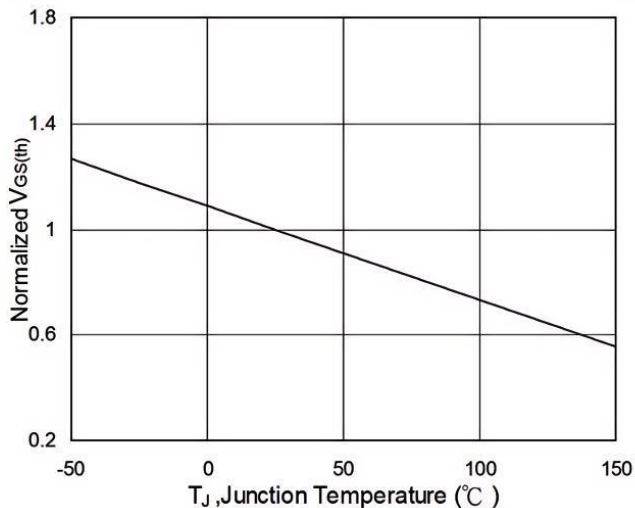


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

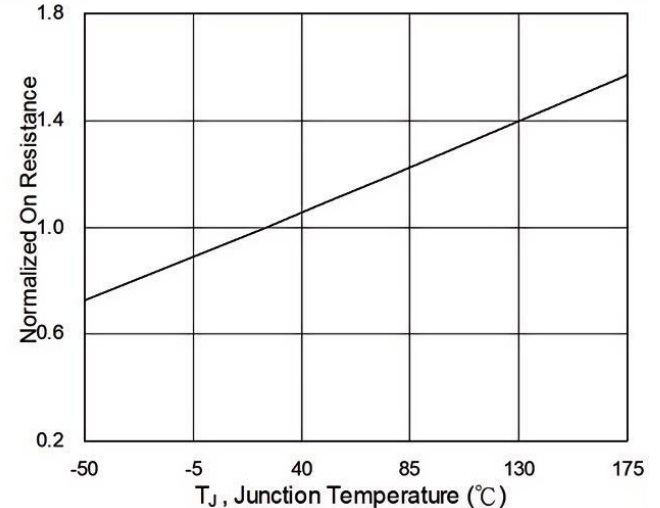


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

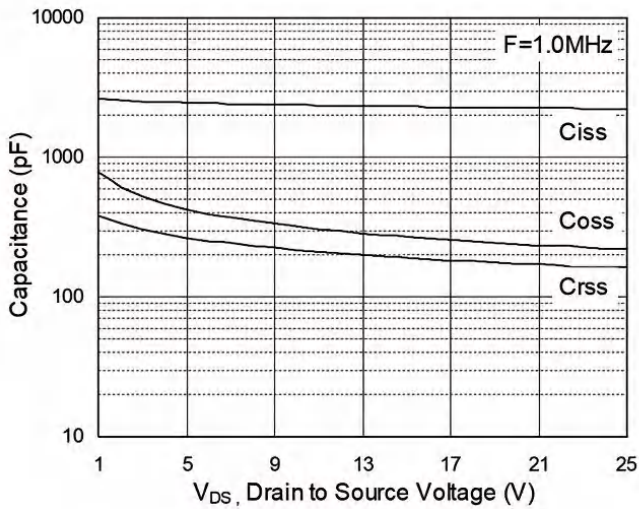


Fig.7 Capacitance

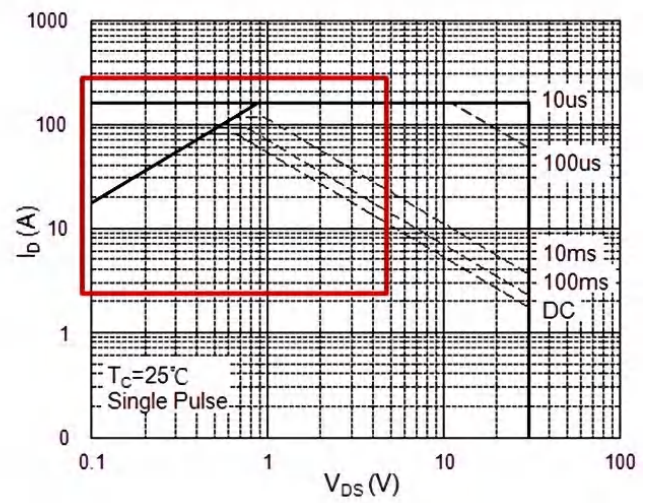


Fig.8 Safe Operating Area

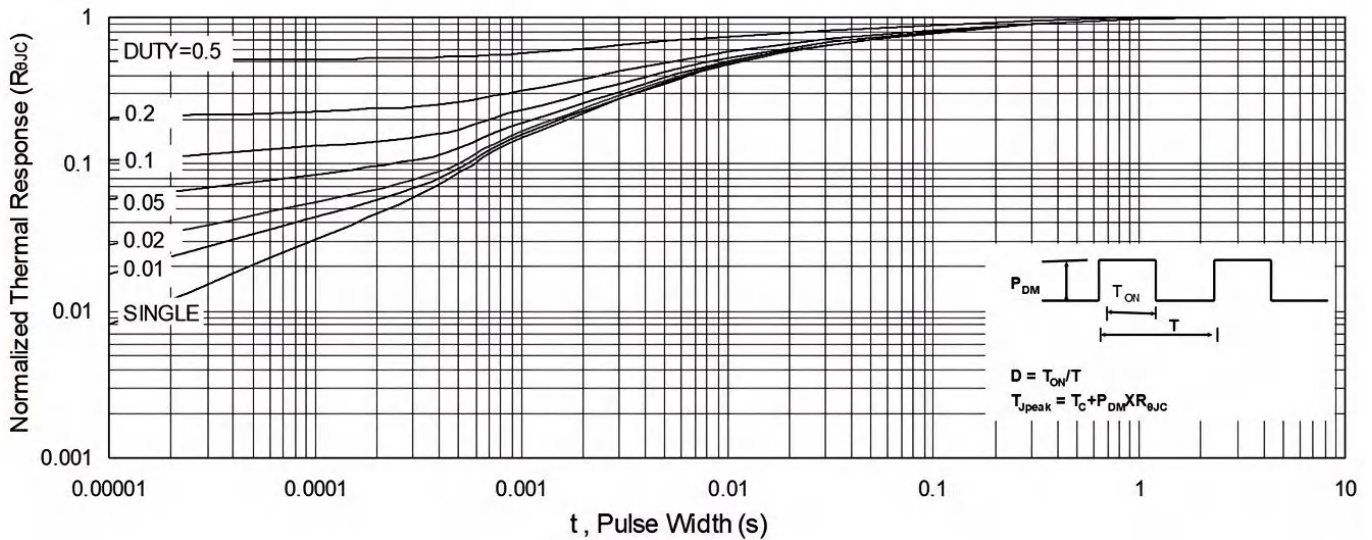


Fig.9 Normalized Maximum Transient Thermal Impedance

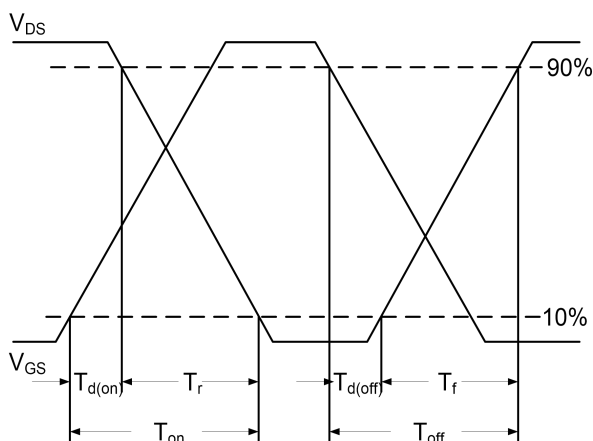


Fig.10 Switching Time Waveform

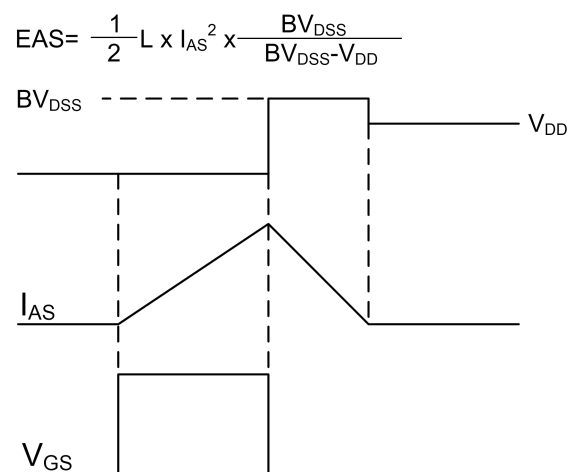


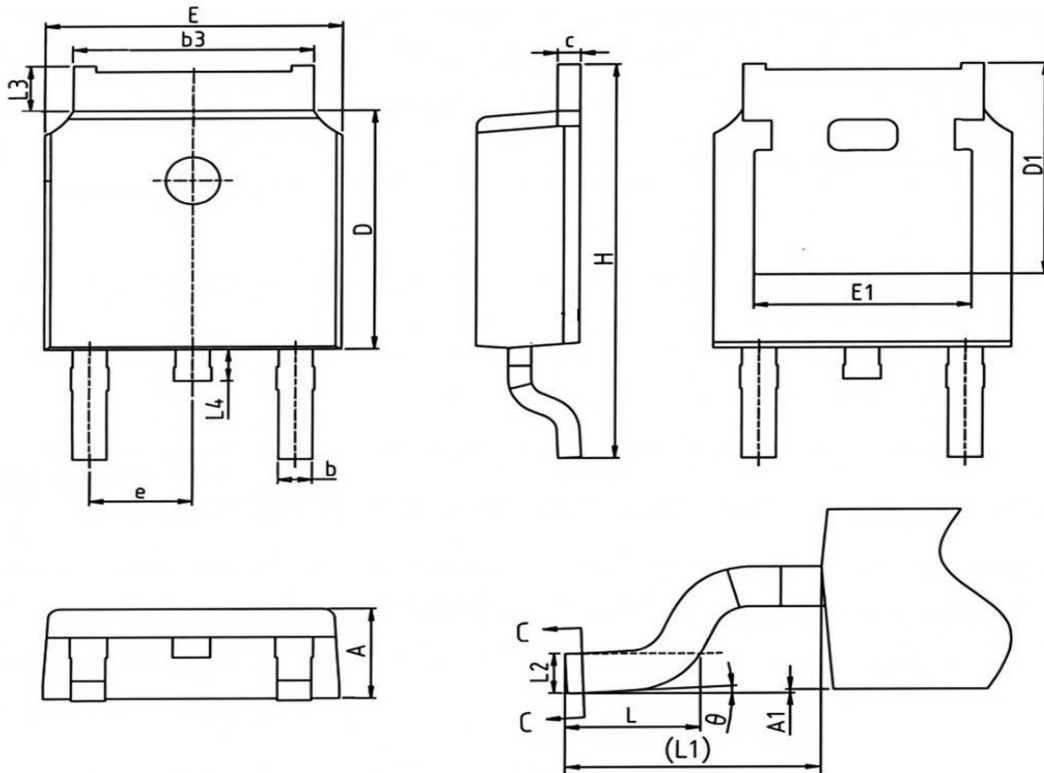
Fig.11 Unclamped Inductive Switching Waveform



Ordering Information

Part Number	Package code	Packaging
HSU80N03	TO252	2500/Tape&Reel

TO252 Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.40	0.086	0.095
A1	-	0.2	-	0.008
b	0.68	0.9	0.026	0.036
b3	4.95	5.46	0.194	0.215
C	0.43	0.89	0.017	0.035
D	5.97	6.22	0.235	0.245
D1	5.300REF		0.209REF	
E	6.35	6.73	0.250	0.265
E1	4.32	---	0.170	-
e	2.286BSC		0.09BSC	
H	9.4	10.5	0.370	0.413
L	1.38	1.78	0.054	0.070
L1	2.90REF		0.114REF	
L2	0.51BSC		0.020BSC	
L3	0.88	1.28	0.034	0.050
L4	0.5	1	0.019	0.039
θ	0°	8°	0°	8°



HSU80N03 Marking:

